

# **NPN Darlington Transistor**

This device is designed for applications requiring extremely high current gain at collector currents to 1.0 A. Sourced from Process 05. See MPSA14 for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
Ic	Collector Current - Continuous	1.2	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max			Units
	W 1007	MPSA13	*MMBTA13	**PZTA13	COM
P <sub>D</sub>	Total Device Dissipation	625	350	1,000	mW
	Derate above 25°C	5.0	2.8	8.0	mW/°C
R <sub>0JC</sub>	Thermal Resistance, Junction to Case	83.3		N 10	°C/W
R <sub>0JA</sub>	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

\*\*Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

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NPN Darlington	Transistor (continued)

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Electr	ical Characteristics	- 25°C unless otherwise noted	WW	W.100X	CON
Symbol	Parameter	Test Conditions	Min	Max	Units
Ісво	Voltage Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$		100	nA
Гево	Emitter-Cutoff Current	$V_{EB} = 10 \text{ V}, \text{ I}_{C} = 0$		100	nA
	RACTERISTICS*	WWW.100Y.COM.T	N	WW	W.100
	DO O HILLO I	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$	5,000		
	DC Current Gain	$I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000		1.W.D
h <sub>FE</sub>	Collector-Emitter Saturation Voltage			1.5	V

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SMAL	L SIGNAL CHARACTERISTICS	W.100 F	COM.1	W
f <sub>T</sub>	Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	125	MHz
*Pulse	Test: Pulse Width £ 300 ms, Duty Cycle £ 2.0%	MW.100	V COM.	N.

\*Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 2.0% WWW.100Y.COM.TW WWW.100Y

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Datasheet Identification	Product Status	Definition
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